

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0074] beginning at page 24, line 13 of the specification as filed electronically on October 10, 2003 with the following rewritten version:

[0074] A semiconductor substrate 100 of the semiconductor device includes a semiconductor substrate main unit 105 and a thin portion 210 on the upper surface S_1 [[side]] of the semiconductor substrate 100. The thin portion 210 is positioned between the semiconductor substrate main unit 105, and is thinner than the semiconductor substrate main unit 105. Boundaries B are indicated in Figure 1 (and Figure 7) with phantom lines between the thin portion 210 and the opposite portions of the semiconductor substrate main unit 105. In addition, a recessed portion 200 and an opening 240 in the lower surface S_2 of the semiconductor substrate 100 are formed by means of the thin portion 210 and the semiconductor substrate main unit 105. At least one through hole 220 is formed in the thin portion 210. The thin portion 210 can be formed by dopant infusion or a selective oxide film.